



Product Summary

BV _{DSS}	Max R _{DS(ON)}	Package	Max I _D T _A = +25°C
-100V	1Ω @ V _{GS} = -10V	SOT23	-0.7A
-1007	1.45Ω @ V _{GS} = -6.0V	30123	-0.5A

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

Applications

- **DC-DC Converters**
- Power Management Functions
- **Disconnect Switches**
- Motor Control

100V P-CHANNEL ENHANCEMENT MODE MOSFET

Features

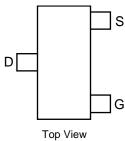
- Fast Switching Speed
- Low Input Capacitance
- Low Gate Charge
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Data Sheet (ZXMP10A13FQ)

Mechanical Data

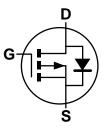
- Case: SOT23 .
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.009 grams (Approximate)



Top View



Pin Out



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMP10A13FTA	SOT23	3,000/Tape & Reel
ZXMP10A13FTC	SOT23	10,000/Tape & Reel

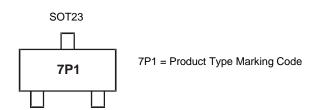
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



and Lead-free



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V _{DSS}	-100	V
Gate-Source Voltage				V _{GS}	±20	V
Continuous Drain Current	V _{GS} = 10V	T _A = +70°C	(Note 6) (Note 6) (Note 6)	ID	-0.7 -0.5 -0.6	A
Pulsed Drain Current (Note 7)			I _{DM}	-3.1	А	
Continuous Source Current (Body Diode) (Note 5)				Is	-1.1	A
Pulsed Source Current (Body Diode) (Note 7)				I _{SM}	-3.1	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	PD	625 5	mW mW/°C
Power Dissipation (Note 6) Linear Derating Factor	PD	806 6.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{θJL}	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

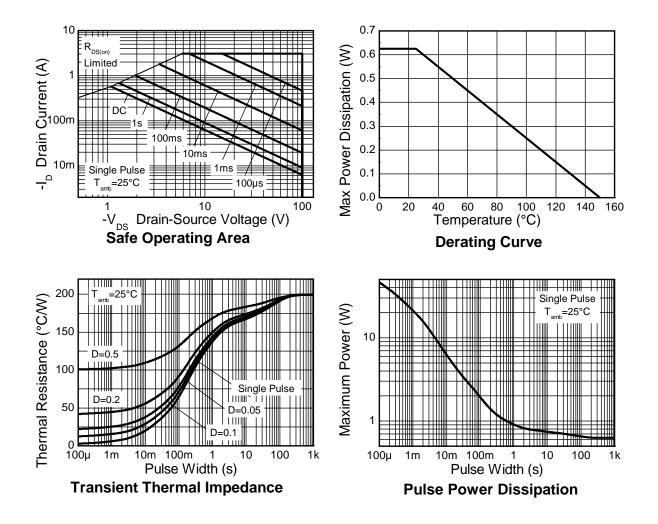
Notes:

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
6. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10µs - pulse current limited by maximum junction temperature.

8. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics (Continued)





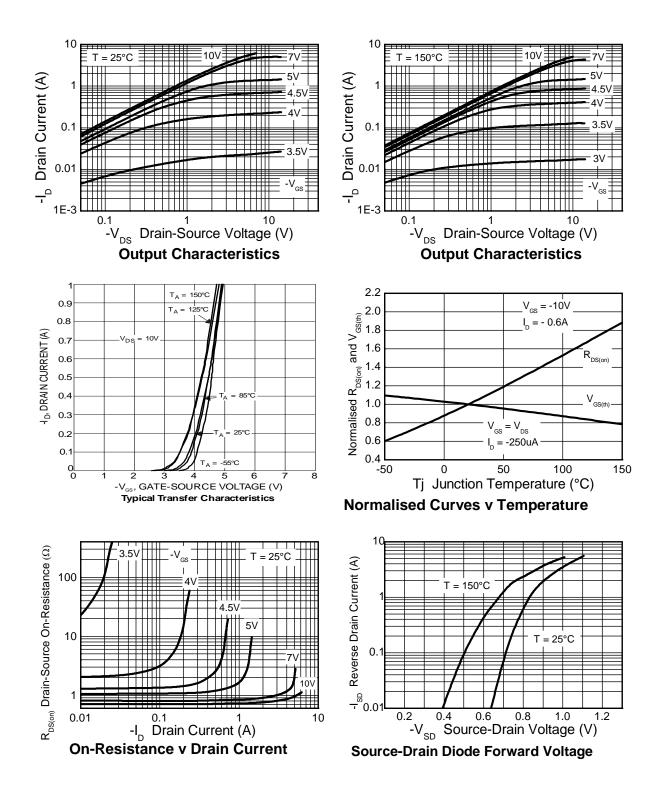
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-100	_	_	V	$I_{D} = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1.0	μA	$V_{DS} = -100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS			•			·	
Gate Threshold Voltage	V _{GS(TH)}	-2.0	_	-4.0	V	$I_D = -250\mu A$, $V_{DS} = V_{GS}$	
Statia Drain Source On Registeres (Note 0)	D	_		1.0	Ω	$V_{GS} = -10V, I_D = -0.6A$	
Static Drain-Source On-Resistance (Note 9)	R _{DS(ON)}			1.45		$V_{GS} = -6.0V, I_D = -0.5A$	
Forward Transconductance (Notes 9 & 11)	g fs		1.2	_	S	V _{DS} = -15V, I _D = -0.6A	
Diode Forward Voltage (Note 9)	V _{SD}		-0.85	-0.95	V	$T_J = +25^{\circ}C, I_S = -0.75A, V_{GS} = 0V$	
Reverse Recovery Time (Note 11)	t _{RR}	_	29	_	ns	T _J = +25°C, I _F = -0.9A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 11)	Q _{RR}		31		nC		
DYNAMIC CHARACTERISTICS (Note 11)			•			·	
Input Capacitance	C _{ISS}		141	_			
Output Capacitance	C _{OSS}	_	13.1	_	pF	V _{DS} = -50V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{RSS}	_	10.8	_			
Turn-On Delay Time (Note 10)	t _{D(ON)}	_	1.6	_			
Turn-On Rise Time (Note 10)	t _R	_	2.1	_		$V_{DD} = -50V, I_D = -1.0A,$	
Turn-Off Delay Time (Note 10)	t _{D(OFF)}		5.9		ns	$R_G \cong 6.0 \Omega, \ V_{GS} = -10 V$	
Turn-Off Fall Time (Note 10)	t _F		3.3				
Total Gate Charge (Note 10)	Q _G	_	1.8	_	nC	$V_{DS} = -50V, V_{GS} = -5.0V,$ $I_D = -0.6A$	
Total Gate Charge (Note 10)	Q _G	_	3.5	_			
Gate-Source Charge (Note 10)	Q _{GS}		0.6	_	nC	$V_{DS} = -50V, V_{GS} = -10V,$	
Gate-Drain Charge (Note 10)	Q _{GD}		1.6	_	1	I _D = -0.6A	

 9. Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
 10. Switching characteristics are independent of operating junction temperature.
 11. For design aid only, not subject to production testing. Notes:

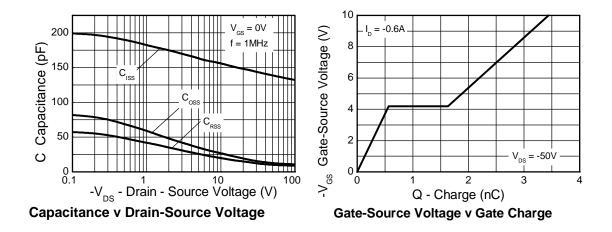


Typical Characteristics

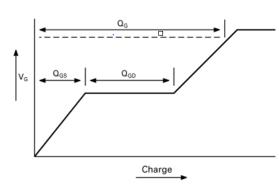




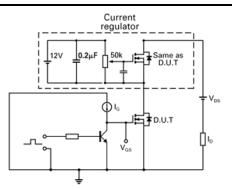
Typical Characteristics (Continued)



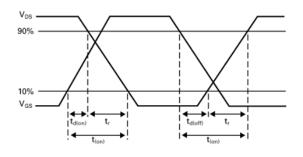
Test Circuits



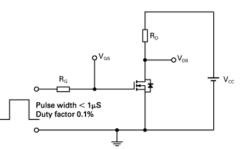
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

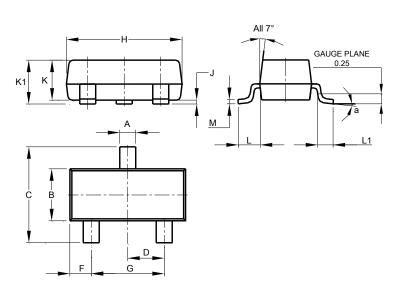


Switching time test circuit



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

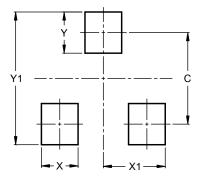


	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Μ	0.085	0.150	0.110				
а	0°	8°	_				
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

SOT23



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